

NPN SILICON LOW POWER TRANSISTOR

DESCRIPTION:

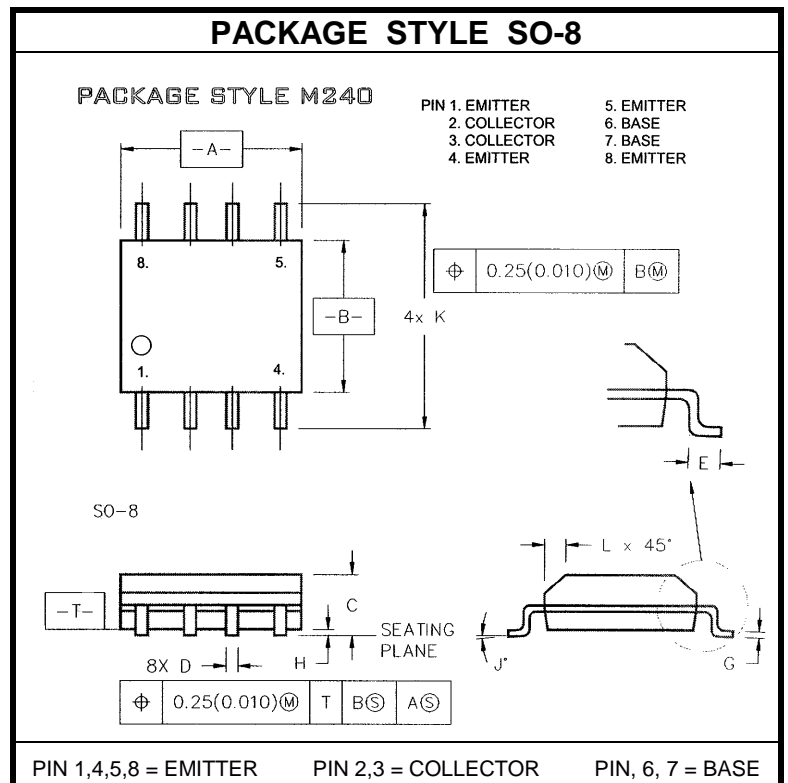
The **ASI MRF8372** is Designed for Wideband large signal stages in the 800 MHz and UHF frequency ranges.

FEATURES:

- $P_{OUT} = 750 \text{ mW}$
- $P_G = 8.0 \text{ dB min.}$
- $\eta = 60\%$ typical
- R1 suffix – Tape and Reel, 500 units
- R2 suffix – Tape and Reel, 2500 units

MAXIMUM RATINGS

I_C	200 mA
V_{CB0}	30 V
V_{CEO}	16 V
V_{EBO}	3.0 V
P_{DISS}	2.2 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	45 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 5.0 \text{ mA}$		30			V
BV_{CEO}	$I_C = 5.0 \text{ mA}$		16			V
BV_{EBO}	$I_E = 0.1 \text{ mA}$		3.0			V
I_{CES}	$V_{CE} = 15 \text{ V}$.0	mA
h_{FE}	$V_{CE} = 5.0 \text{ V}$	$I_C = 50 \text{ mA}$	30		200	---
C_{OB}	$V_{CB} = 15 \text{ V}$	$f = 1.0 \text{ MHz}$			2.75	pF
P_G	$V_{CE} = 12.5 \text{ V}$	$P_{OUT} = 0.75 \text{ W}$	8.0	9.5		dB
η_c		$f = 870 \text{ MHz}$	50	60		%

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